

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY

| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) | Q _g (Typ.) |
|---------------------|----------------------------------|--------------------|-----------------------|
| 100 | 0.055 at V _{GS} = 10 V | 25 | 21nC |
| | 0.057 at V _{GS} = 4.5 V | 25 | |
| | | | |

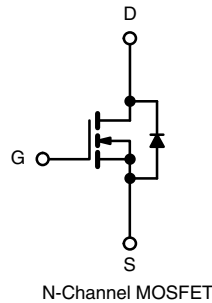
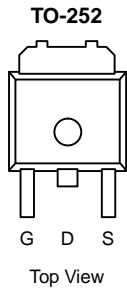
FEATURES

- TrenchFET® power MOSFET
- 100 % UIS tested


RoHS
 COMPLIANT

APPLICATIONS

- Primary side switch



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNIT |
|--|------------------------|-----------------------------------|---------------------|------|
| Drain-Source Voltage | | V _{DS} | 100 | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | |
| Continuous Drain Current (T _J = 175 °C) | T _C = 25 °C | I _D | 25 | A |
| | T _C = 70 °C | | 20 | |
| | T _A = 25 °C | | 12 ^{b, c} | |
| | T _A = 70 °C | | 10 ^{b, c} | |
| Pulsed Drain Current | | I _{DM} | 75 | |
| Continuous Source-Drain Diode Current | T _C = 25 °C | I _S | 50 ^e | |
| | T _A = 25 °C | | 6.9 ^{b, c} | |
| Avalanche Current Pulse | L = 0.1 mH | I _{AS} | 33 | mJ |
| Single Pulse Avalanche Energy | | E _{AS} | 55 | |
| Maximum Power Dissipation | T _C = 25 °C | P _D | 83 | W |
| | T _C = 70 °C | | 58 | |
| | T _A = 25 °C | | 8.3 ^{b, c} | |
| | T _A = 70 °C | | 5.8 ^{b, c} | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +175 | °C |

THERMAL RESISTANCE RATINGS

| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT |
|---|--------------|-------------------|---------|---------|------|
| Maximum Junction-to-Ambient ^{b, d} | t ≤ 10 s | R _{thJA} | 15 | 18 | °C/W |
| Maximum Junction-to-Case | Steady State | R _{thJC} | 1.5 | 1.8 | |

Notes

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 50 °C/W.
- Calculated based on maximum junction temperature. Package limitation current is 50 A.

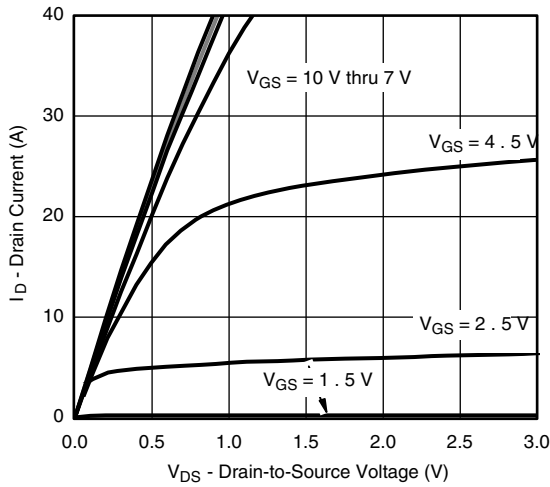
| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|---|--------------------------------------|--|------|-------|-------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | 100 | - | - | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | I _D = 250 μA | - | 165 | - | mV/°C |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | | - | -11 | - | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | 0.8 | 1.2 | 1.6 | V |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 100 V, V _{GS} = 0 V | - | - | 1 | μA |
| | | V _{DS} = 100 V, V _{GS} = 0 V, T _J = 55 °C | - | - | 10 | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = 10 V | 25 | - | - | A |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 10 V, I _D =12A | - | 0.055 | | Ω |
| | | V _{GS} =4.5 V, I _D =8A | | 0.057 | | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = 15 V, I _D = 12 A | - | 25 | - | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 12 V, V _{GS} = 0 V, f = 1 MHz | - | 1800 | - | pF |
| Output Capacitance | C _{oss} | | - | 180 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 60 | - | |
| Total Gate Charge | Q _g | V _{DS} = 50 V, V _{GS} = 10 V, I _D = 12 A | - | 21 | 32 | nC |
| Gate-Source Charge | Q _{gs} | | - | 10 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 9 | - | |
| Gate Resistance | R _g | f = 1 MHz | - | 1.5 | - | Ω |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 50 V, R _L = 5 Ω I _D ≡ 10 A, V _{GEN} = 10 V, R _g = 1 Ω | - | 10 | 15 | ns |
| Rise Time | t _r | | - | 10 | 15 | |
| Turn-Off Delay Time | t _{d(off)} | | - | 15 | 25 | |
| Fall Time | t _f | | - | 10 | 15 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | - | - | 50 | A |
| Pulse Diode Forward Current ^a | I _{SM} | | - | - | 40 | |
| Body Diode Voltage | V _{SD} | I _S = 10 A | - | 0.8 | 1.2 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C | - | 50 | 75 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | - | 100 | 150 | nC |
| Reverse Recovery Fall Time | t _a | | - | 38 | - | ns |
| Reverse Recovery Rise Time | t _b | | - | 12 | - | |

Note

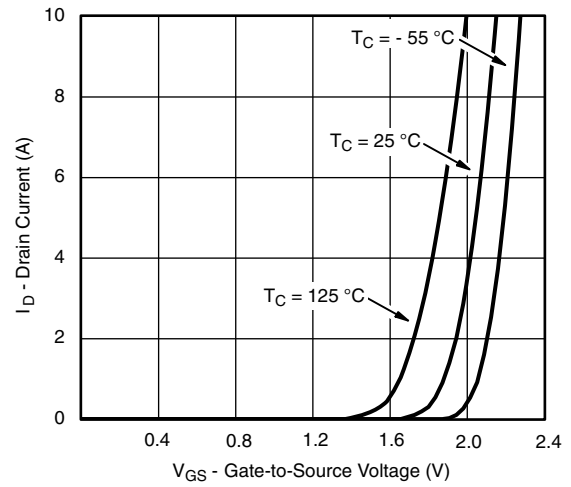
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

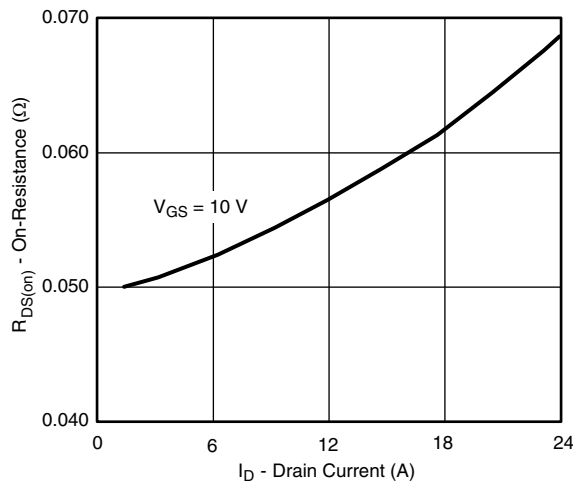
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



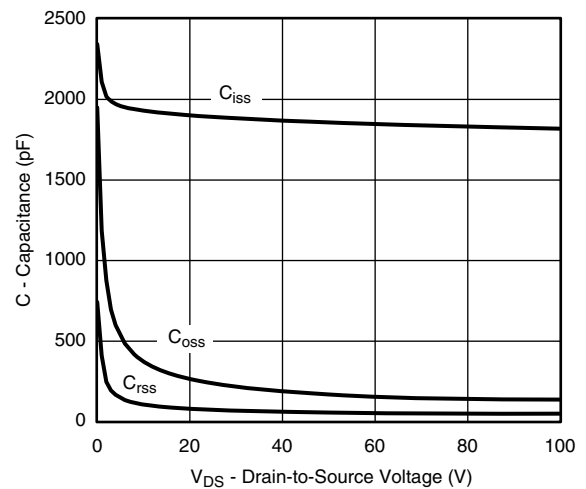
Output Characteristics



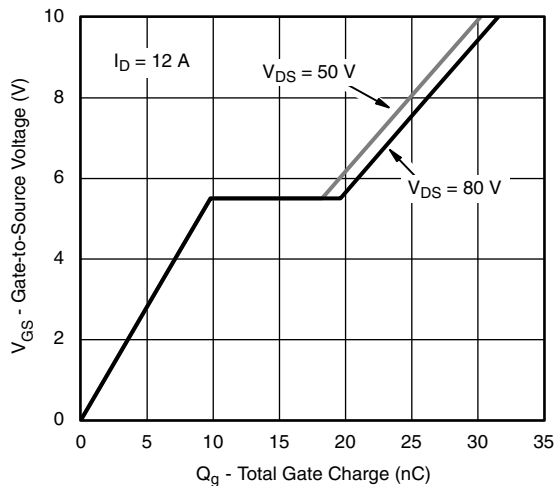
Transfer Characteristics



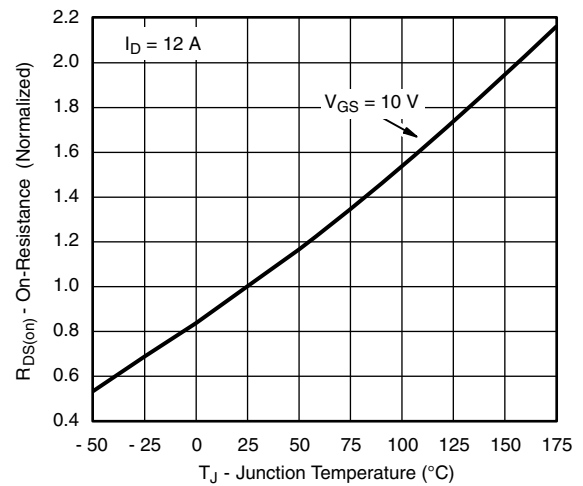
On-Resistance vs. Drain Current



Capacitance

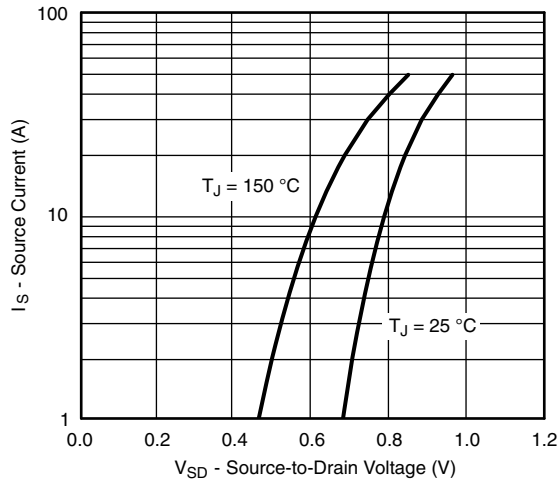


Gate Charge

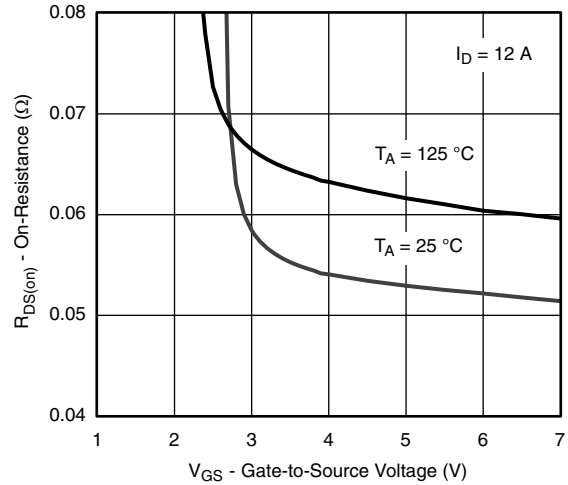


On-Resistance vs. Junction Temperature

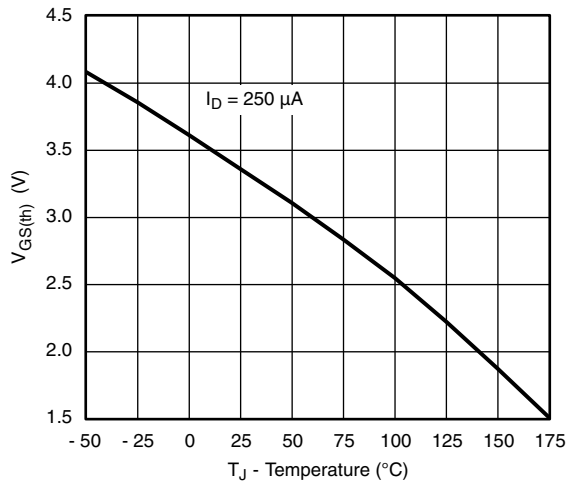
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



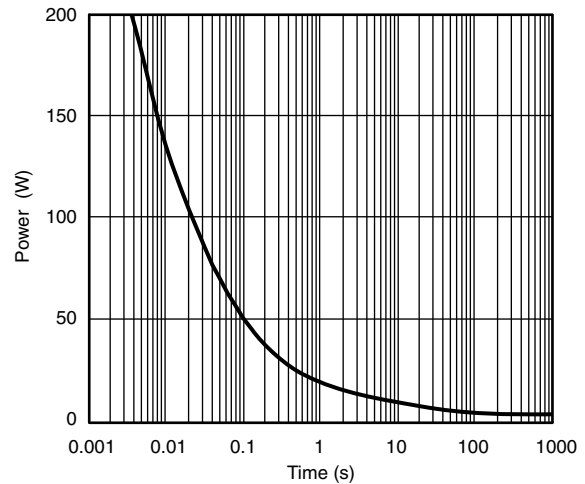
Source-Drain Diode Forward Voltage



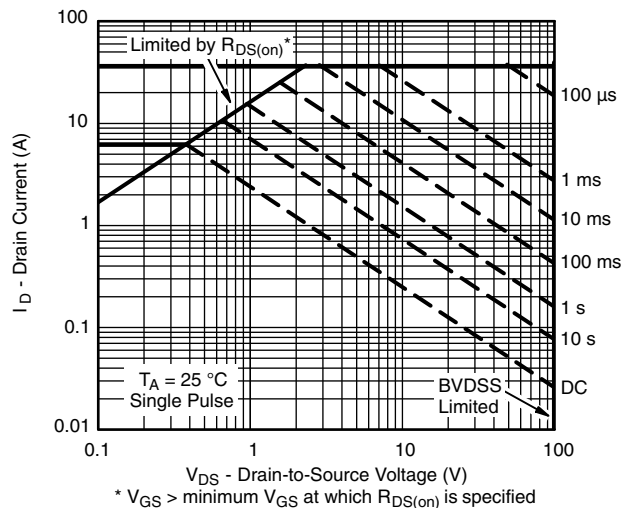
$R_{DS(on)}$ vs. V_{GS} vs. Temperature



Threshold Voltage

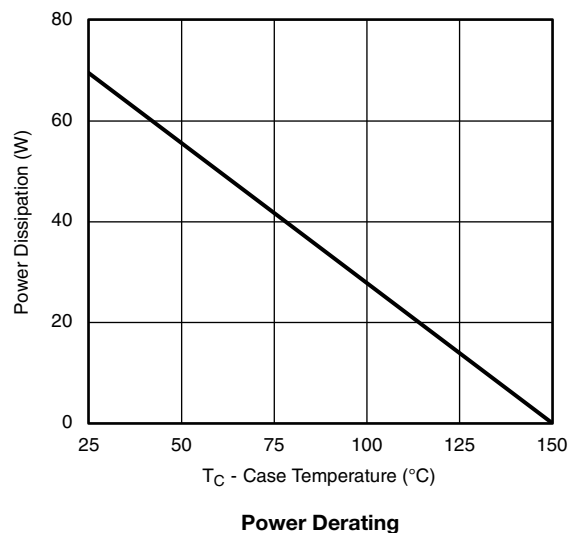
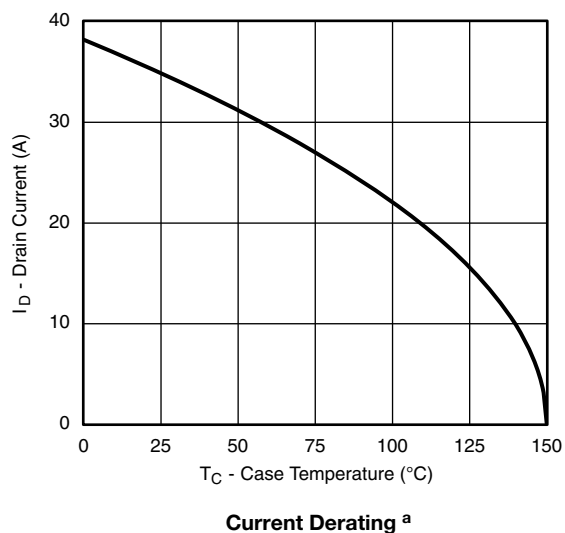


Single Pulse Power, Junction-to-Ambient



Safe Operating Area

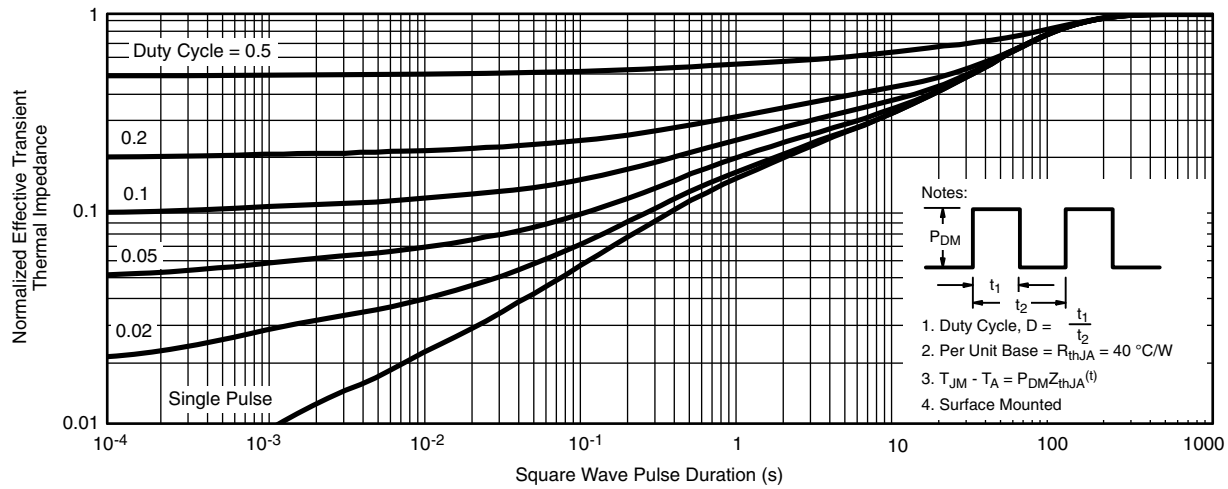
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



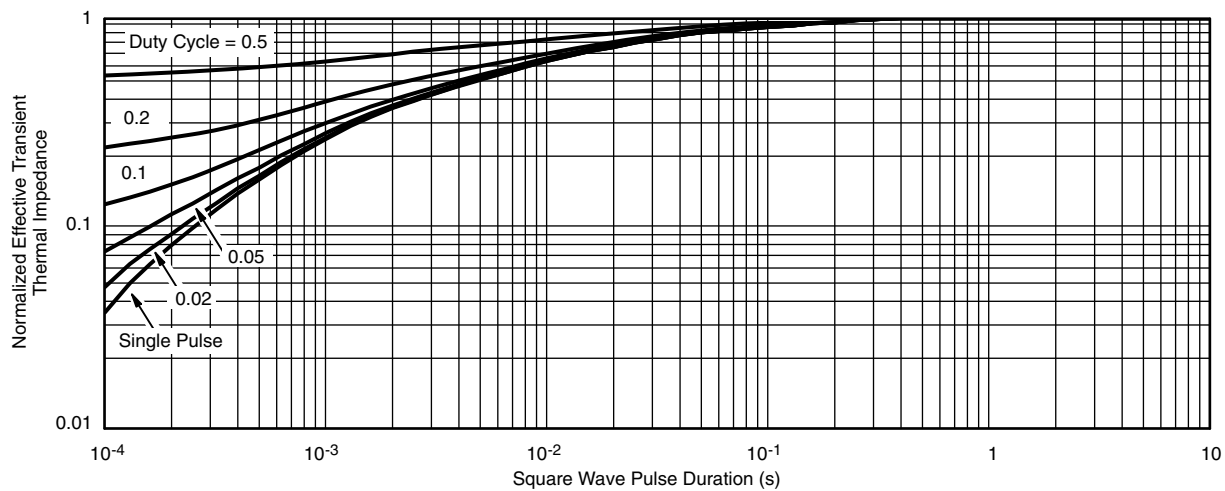
Note

- The power dissipation P_D is based on T_J (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

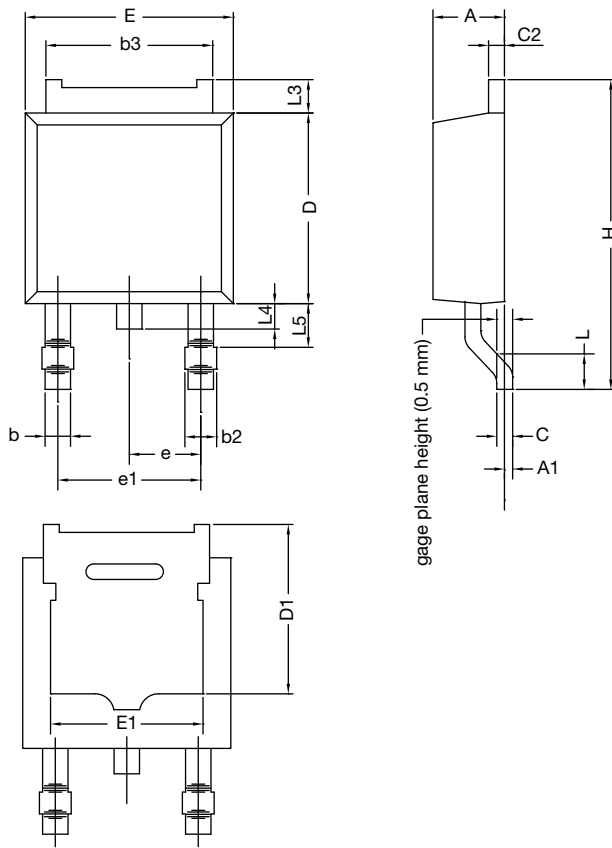


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252AA Case Outline

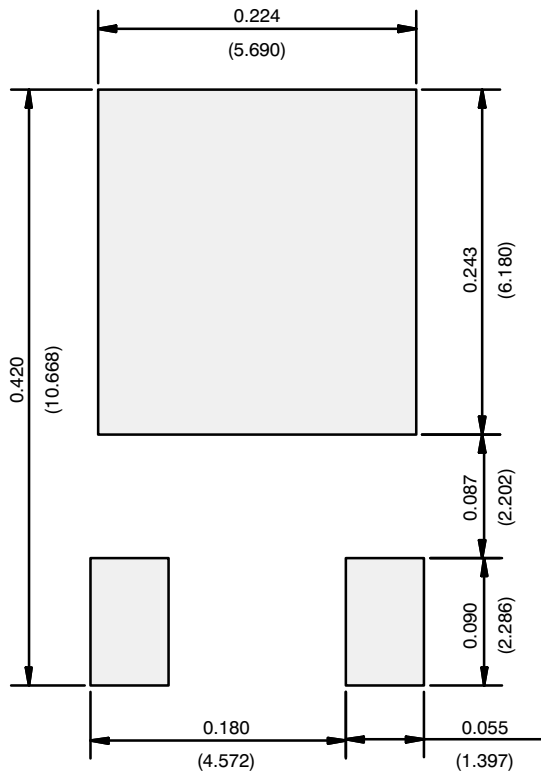


| DIM. | MILLIMETERS | | INCHES | |
|--|-------------|-------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 2.18 | 2.38 | 0.086 | 0.094 |
| A1 | - | 0.127 | - | 0.005 |
| b | 0.64 | 0.88 | 0.025 | 0.035 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 |
| C | 0.46 | 0.61 | 0.018 | 0.024 |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 4.10 | - | 0.161 | - |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | - | 0.170 | - |
| H | 9.40 | 10.41 | 0.370 | 0.410 |
| e | 2.28 BSC | | 0.090 BSC | |
| e1 | 4.56 BSC | | 0.180 BSC | |
| L | 1.40 | 1.78 | 0.055 | 0.070 |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 |
| L4 | - | 1.02 | - | 0.040 |
| L5 | 1.01 | 1.52 | 0.040 | 0.060 |
| ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347 | | | | |

Notes

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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